



68V N-Channel Trench MOSFET

Features		Product Summary		
Trench Power Technology		VDS 68V		
• Low R _{DS(ON)}		R _{DS(ON)} (at V _{GS} =10V)) < 7.5mΩ	
Low Gate Charge				
 Optimized for Fast-switching Application 	ons	I _D (at V _{GS} =10V)	95A	
Applications				
 Synchronous Rectification in DC/DC and AC/DC Converters 		100% UIS Tested		IIC
Isolated DC/DC Converters in Telecor	n and Industrial		Ko	ns
TO-263 G D S G	B	rO-220 © p s	Drain Gate	
Device	Package		Marking	
TTB95N68A	TO-2	63	95N68A	
TTD95N68A	TO-252		95N68A	
TTP95N68A	TO-2	20	95N68A	
Absolute Maximum Ratings	Γ _C = 25ºC, unless c	therwise noted		
Parameter		Symbol	Value	Uni
Drain-Source Voltage (V _{GS} = 0V)		V _{DSS}	68	V
Continuous Drain Current	$T_{\rm C} = 25^{\rm o}{\rm C}$		95	
Continuous Drain Current	$T_{\rm C} = 100^{\circ}{\rm C}$	I _D	66	A
Pulsed Drain Current (note1)		I _{DM}	380	A
Gate-Source Voltage		V _{GSS}	±20	V
Single Pulse Avalanche Energy (note2)		E _{AS}	380	mJ
Avalanche Current		I _{As}	37	A
	T _C = 25°C	P _D	130.5	W
Power Dissipation (note3)	$T_{\rm C} = 100^{\circ}{\rm C}$		65.5	W
	-			
Power Dissipation (note3) Operating Junction and Storage Temperat	-	T _J , T _{stg}	-55~+175	°C
	-	T _J , T _{stg}	-55~+175	0°C
Operating Junction and Storage Temperat	-	T _J , T _{stg} Symbol	-55~+175 Value	
Operating Junction and Storage Temperat	-			



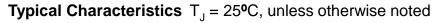
Specifications $T_J = 25^{\circ}C$, u	unless othe	rwise noted				
Parameter		Test Conditions	Value			
	Symbol		Min.	Тур.	Max.	Unit
Static	•					
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0V, I_{D} = 250\mu A$	68			V
		$V_{DS} = 68V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			1	μA
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 68V, V_{GS} = 0V, T_{J} = 100^{\circ}C$			25	
Gate-Source Leakage	I _{GSS}	$V_{GS} = \pm 20V$			±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	3	4	V
Drain-Source On-Resistance	R _{DS(on)}	$V_{GS} = 10V, I_{D} = 30A$		6.5	7.5	mΩ
Forward Transconductance	9 _{fs}	$V_{DS} = 5V, I_{D} = 20A$	20			S
Dynamic	-					
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 30V,		4169		pF
Output Capacitance	C _{oss}			274		
Reverse Transfer Capacitance	C _{rss}	f = 1.0MHz		222		
Total Gate Charge	Qg			70		nC
Gate-Source Charge	Q _{gs}	$V_{DD} = 30V, I_{D} = 20A, V_{GS} = 10V$		20		
Gate-Drain Charge	Q _{gd}			18		
Turn-on Delay Time	t _{d(on)}			15		ns
Turn-on Rise Time	t _r	V _{DD} = 30V, I _D = 30A,		94		
Turn-off Delay Time	t _{d(off)}	$R_{\rm G} = 2.5\Omega$		46		
Turn-off Fall Time	t _f			32		
Drain-Source Body Diode Characte	ristics			•		
Continuous Body Diode Current	۱ _s				95	•
Pulsed Diode Forward Current	I _{SM}	T _C = 25°C			380	A
Body Diode Voltage	V _{SD}	$T_J = 25^{\circ}C, I_{SD} = 20A, V_{GS} = 0V$			1.2	V
Reverse Recovery Time	t _{rr}	I _F = 20A,		78		ns
Reverse Recovery Charge	Q _{rr}	di _F /dt = 100A/µs		51		nC

Notes

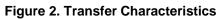
- 1. Repetitive Rating: Pulse Width limited by maximum junction temperature
- 2. $I_{AS} = 37A$, $V_{DD} = 50V$, $R_G = 25\Omega$, Starting $T_J = 25^{\circ}C$
- 3. The power dissipation PD is based on TJ(MAX)=175° C, using junction-to-case thermal resistance.

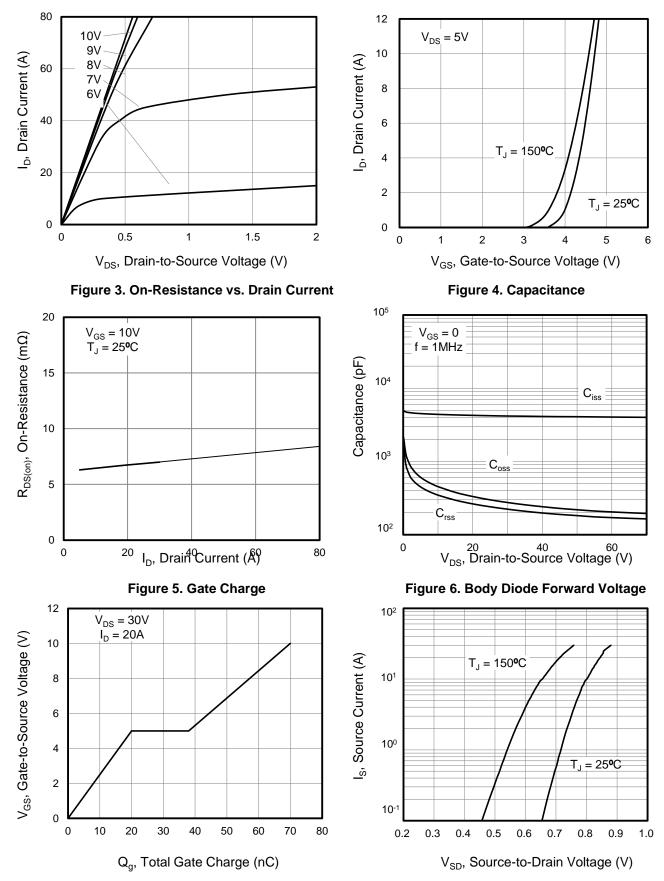
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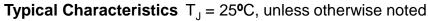


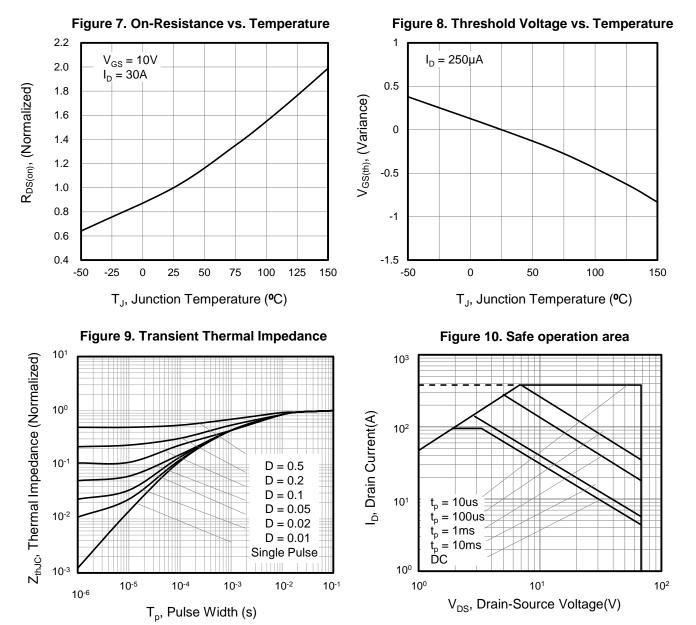




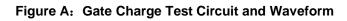












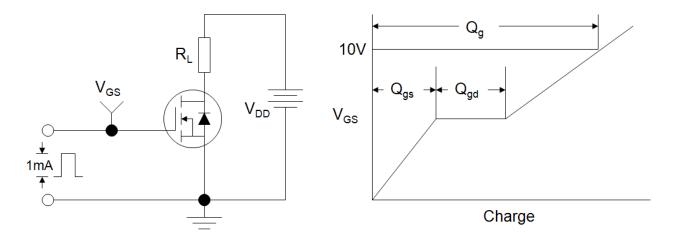


Figure B: Resistive Switching Test Circuit and Waveform

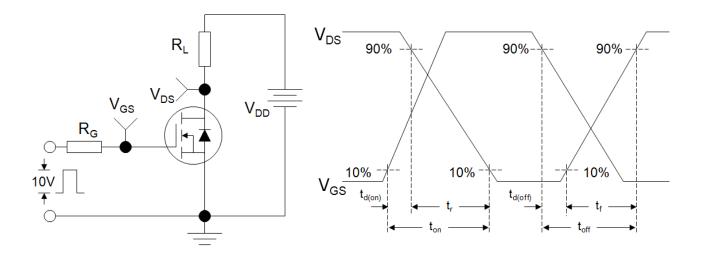
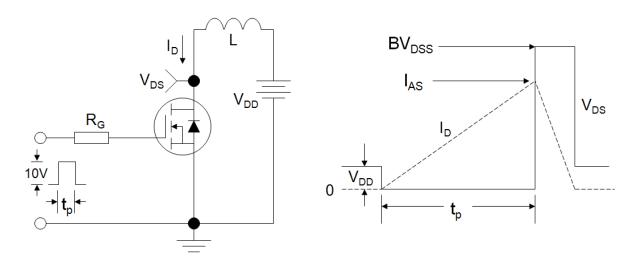
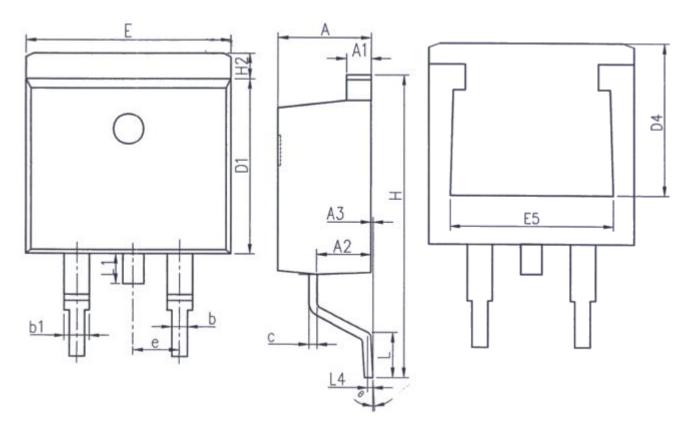


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





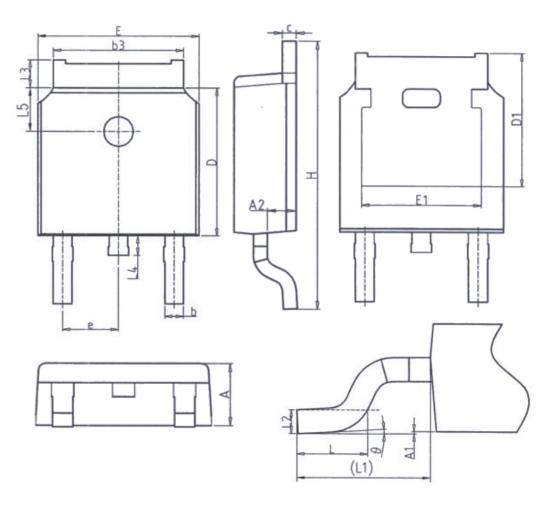
TO-263



	Unit: mm	_	l	Unit: mm	n
Symbol	Min.	Max.	Symbol	Min. Max.	
Α	4. 37	4. 77	E	9.86	10.36
A1	1.22	1.42	E5	7.06	-
A2	2.49	2.89	е	2. 54BSC	
A3	0.00	0. 25	Н	14.70	15.50
b	0.70	0.96	H2	1.07	1.47
b1	1.17	1.47	L	2.00	2.60
с	0.30	0.53	L1	1.40	1.70
D1	8.50	8.90	L4	0. 25BSC	
D4	6. 60	-	θ	0° 9°	



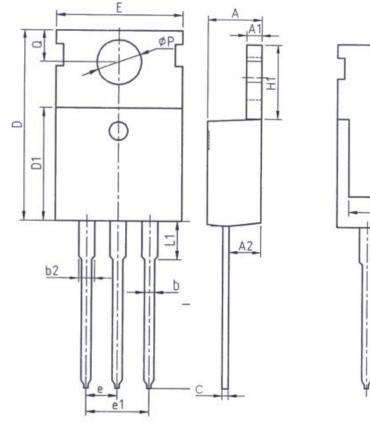
TO-252

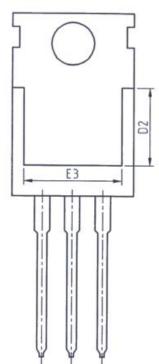


Unit: mm			
Symbol	Min.	Max.	
Α	2.20	2.40	
A1	0.00	0.20	
A2	0.97	1.17	
b	0.68	0.90	
b3	5.20	5.50	
с	0.43	0.63	
D	5.98	6. 22	
D1	5. 30REF		
E	6.40	6.80	
E1 4.63 -			

Unit: mm			
Symbol	Min. Max.		
e	2. 286BSC		
Н	9.40	10.50	
L	1.38	1.75	
L1	2.90REF		
L2	0. 51BSC		
L3	0.88	1.28	
L4	_	1.00	
L5	1.65	1.95	
θ	0° 8°		

TO-220





Unit: mm			
Symbol	Min. Max.		
Α	A 4.37		
A1	1.25	1.45	
A2	2. 20	2.60	
b	0. 70	0.95	
b2	1.17	1.47	
С	0.40	0.65	
D	15.10	16.10	
D1	8.80	9.40	
D2	5.50	_	

Unit: mm			
Symbol	Min. Max.		
E	9.70 10.30		
E3	7.00 -		
e	2. 54BSC		
e1	5. 08BSC		
H1	6.25 6.85		
L	12.75	13.80	
L1	I	3. 40	
Р	3.40 3.80		
Q	2.60 3.00		

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